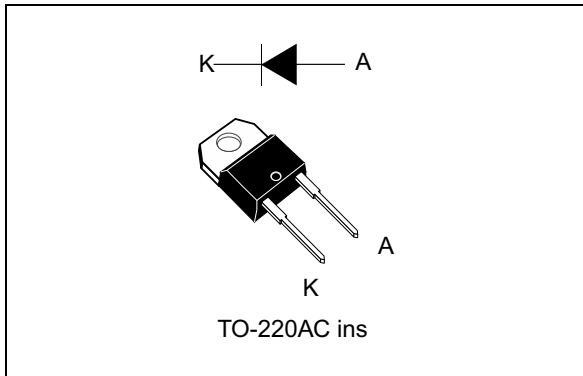


600 V tandem extra fast diode

Datasheet – production data


Features

- High voltage rectifier
- Tandem diodes in series
- Very low switching losses
- Insulated device with internal ceramic
- Equal thermal conditions for both 300 V diodes
- Static and dynamic equilibrium of internal diodes are warranted by design
- Insulated package:
 - Insulated voltage: 2500 V_{RMS} sine

Description

This device is part of ST's second generation of 600 V tandem diodes. It has ultralow switching-losses with a minimized Q_{RR} that makes it perfect for use in circuits working in hard-switching mode. In particular the V_F/Q_{RR} trade-off positions this device between standard ultrafast diodes and silicon-carbide Schottky rectifiers in terms of price/performance ratio.

The device offers a new positioning giving more flexibility to power-circuit designers looking for good performance while still respecting cost constraints.

Featuring ST's Turbo 2 600 V technology, the device is particularly suited as a boost diode in continuous conduction mode power factor correction circuits.

Table 1. Device summary

Symbol	Value
$I_{F(AV)}$	8 A
V_{RRM}	600 V
t_{rr} (typ)	13 ns
I_{RM} (typ)	2 A
V_F (typ)	2.5 V
I_{FRM}	40 A
T_j (max)	175 °C

1 Characteristics

Table 2. Absolute ratings (limiting values at $T_j = 25\text{ °C}$, unless otherwise specified)

Symbol	Parameter		Value	Unit
V_{RRM}	Repetitive peak reverse voltage	T_j from 25 to 150 °C	600	V
		$T_j = -40\text{ °C}$	550	
$I_{F(RMS)}$	Forward rms current		14	A
$I_{F(AV)}$	Average forward current, $\delta = 0.5$, square wave	$T_c = 80\text{ °C}$	8	A
I_{FSM}	Surge non repetitive forward current	$t_p = 10\text{ ms}$ sinusoidal	55	A
I_{FRM}	Repetitive peak forward current	$T_c = 80\text{ °C}$, $\delta = 0.1$	40	A
T_{stg}	Storage temperature range		-65 to +175	°C
T_j	Operating junction temperature range		-40 to +175	°C

Table 3. Thermal parameters

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	Junction to case	2.9	°C/W

Table 4. Static electrical characteristics

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$I_R^{(1)}$	Reverse leakage current	$T_j = 25\text{ °C}$	$V_R = V_{RRM}$	-	6	μA
		$T_j = 125\text{ °C}$		-	20	
$V_F^{(2)}$	Forward voltage drop	$T_j = 25\text{ °C}$	$I_F = 8\text{ A}$	-	3.4	V
		$T_j = 150\text{ °C}$		-	2.5	

1. Pulse test: $t_p = 5\text{ ms}$, $\delta < 2\%$
2. Pulse test: $t_p = 380\text{ }\mu\text{s}$, $\delta < 2\%$

To evaluate the conduction losses use the following equation:

$$P = 2.2 \times I_{F(AV)} + 0.113 I_{F(RMS)}^2$$

Table 5. Dynamic characteristics

Symbol	Parameter	Test conditions		Min.	Typ.	Max.	Unit
t_{rr}	Reverse recovery time	$T_j = 25\text{ }^\circ\text{C}$	$I_F = 1\text{ A}, V_R = 30\text{ V},$ $di_F/dt = -50\text{ A}/\mu\text{s}$	-	20	26	ns
			$I_F = 8\text{ A}, V_R = 400\text{ V},$ $di_F/dt = -200\text{ A}/\mu\text{s}$	-	13	17	
I_{RM}	Reverse recovery current	$T_j = 125\text{ }^\circ\text{C}$	$I_F = 8\text{ A}, V_R = 400\text{ V},$ $di_F/dt = -200\text{ A}/\mu\text{s}$	-	2	2.6	A
S	Softness factor			-	0.9	-	-
Q_{RR}	Reverse recovery charge	$T_j = 25\text{ }^\circ\text{C}$	$I_F = 8\text{ A}, V_R = 400\text{ V},$ $di_F/dt = -200\text{ A}/\mu\text{s}$	-	4	-	nC
		$T_j = 125\text{ }^\circ\text{C}$		-	20	-	

Figure 1. Average forward power dissipation versus average forward current

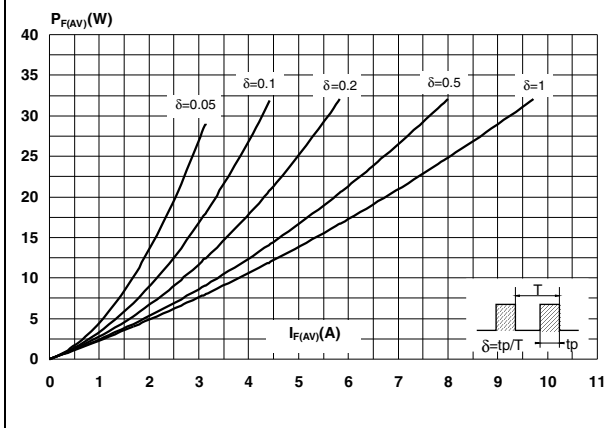


Figure 2. Forward voltage drop versus forward current (typical values)

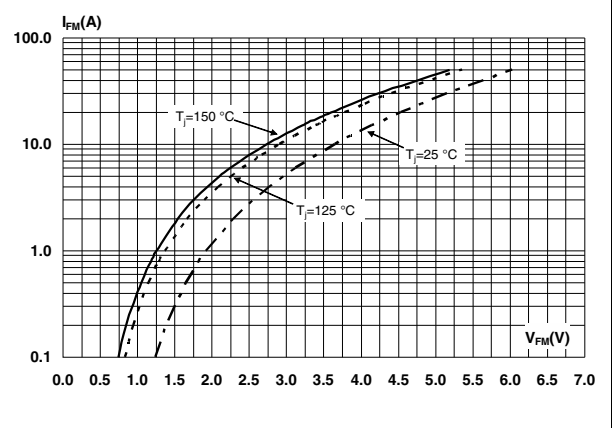


Figure 3. Relative variation of thermal impedance, junction to case, versus pulse duration

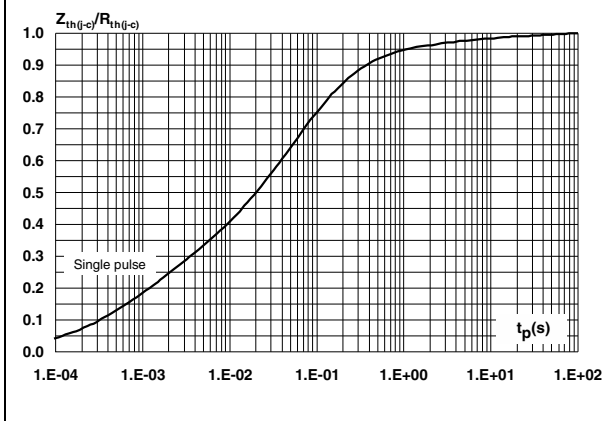


Figure 4. Peak reverse recovery current versus di_F/dt (typical values)

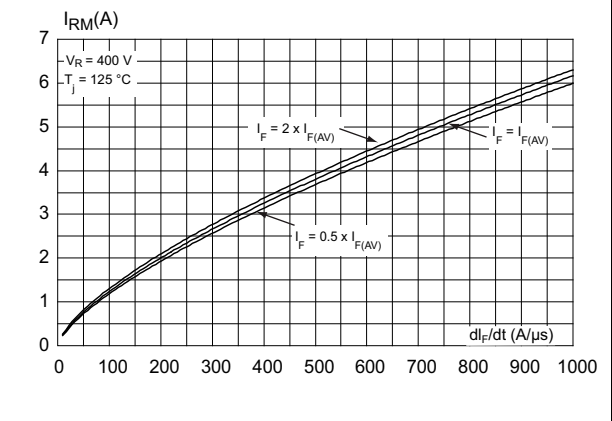


Figure 5. Reverse recovery time versus di_F/dt (typical values)

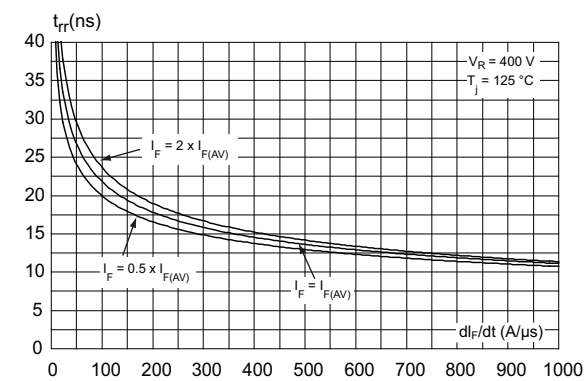


Figure 6. Reverse recovery charges versus di_F/dt (typical values)

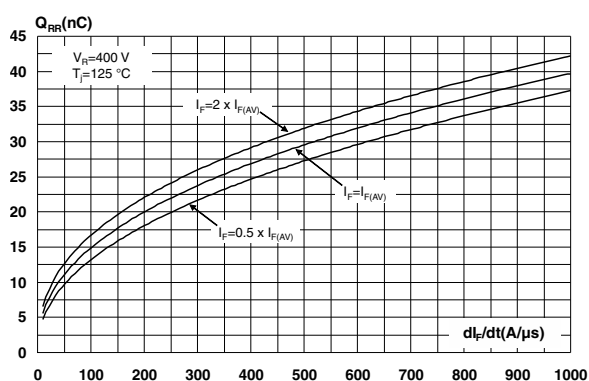


Figure 7. Reverse recovery softness factor versus di_F/dt (typical values)

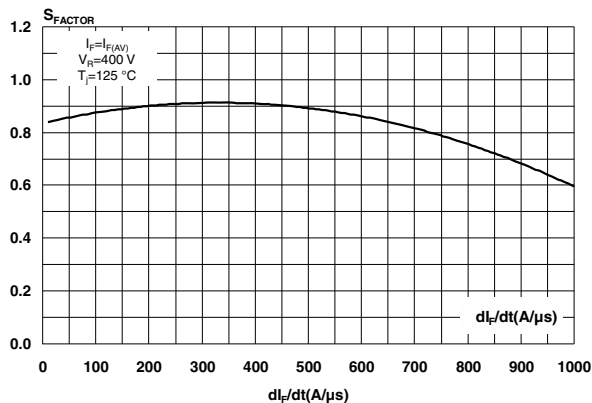


Figure 8. Relative variations of dynamic parameters versus junction temperature

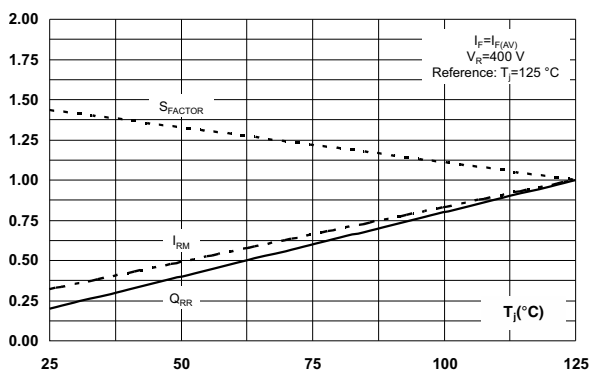


Figure 9. Junction capacitance versus reverse voltage applied (typical values)

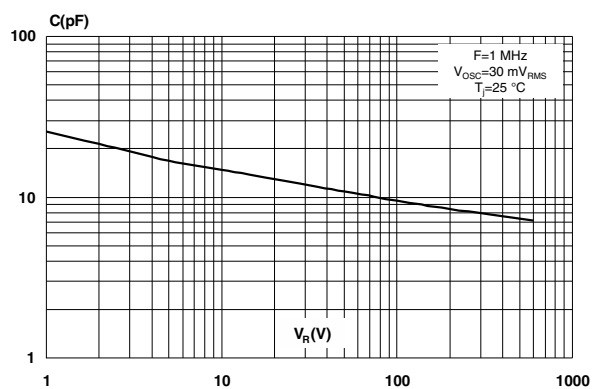


Figure 10. Relative variation of non-repetitive peak surge forward current versus pulse duration

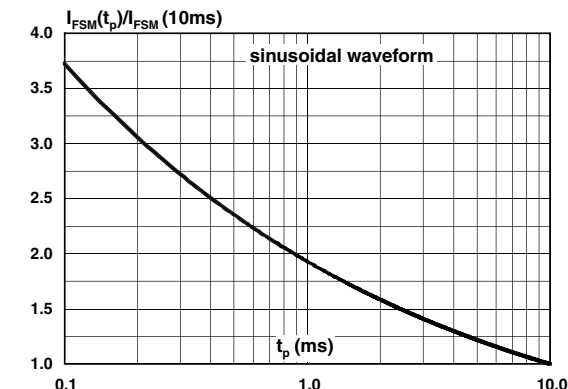
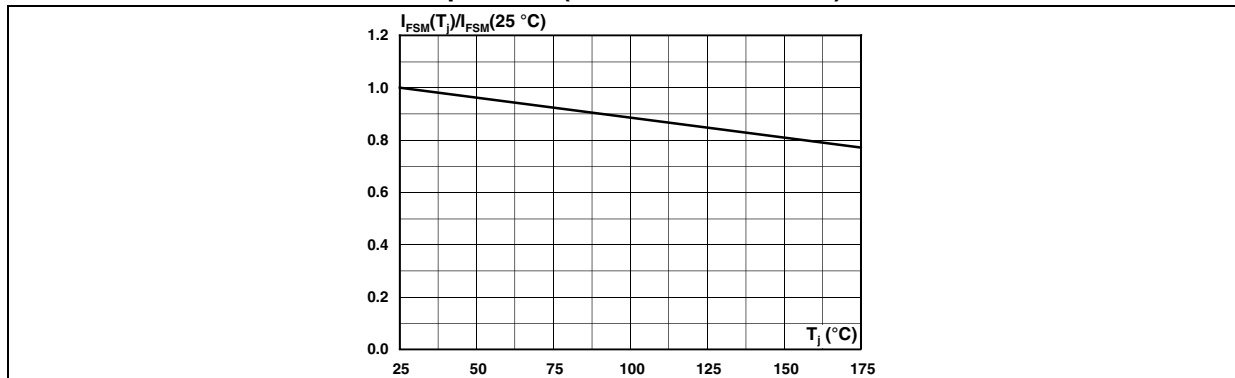


Figure 11. Relative variation of non-repetitive peak surge forward current versus initial junction temperature (sinusoidal waveform)



2 Package information

- Epoxy meets UL94, V0
- Cooling method: by conduction (C)
- Recommended torque: 0.55 N·m
- Maximum torque: 0.7 N·m

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK® is an ST trademark.

2.1 TO-220AC ins. package information

Figure 12. TO-220AC ins. package outline

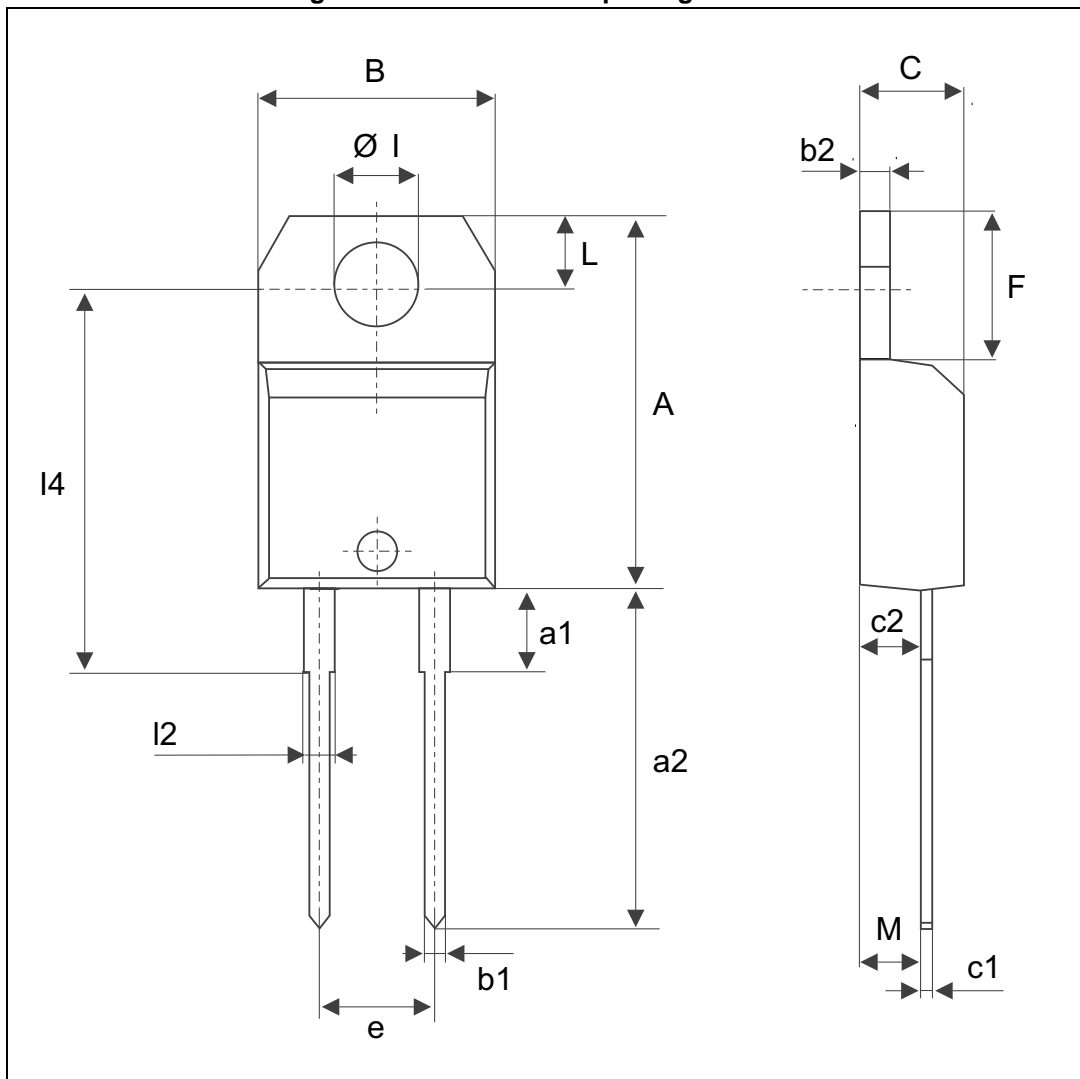


Table 6. T0-220AC ins. package mechanical data

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	15.20		15.90	0.598		0.625
a1		3.75			0.147	
a2	13.00		14.00	0.511		0.551
B	10.00		10.40	0.393		0.409
b1	0.61		0.88	0.024		0.034
b2	1.23		1.32	0.048		0.051
C	4.40		4.60	0.173		0.181
c1	0.49		0.70	0.019		0.027
c2	2.40		2.72	0.094		0.107
e	4.80		5.40	0.189		0.212
F	6.20		6.60	0.244		0.259
ØI	3.75		3.85	0.147		0.151
I4	15.80	16.40	16.80	0.622	0.646	0.661
L	2.65		2.95	0.104		0.116
I2	1.14		1.70	0.044		0.066
M		2.60			0.102	

3 Ordering information

Table 7. Ordering information

Order code	Marking	Package	Weight	Base qty	Delivery mode
STTH8ST06DI	STTH8ST06DI	TO-220AC ins	2.3 g	50	Tube

4 Revision history

Table 8. Document revision history

Date	Revision	Changes
14-May-2013	1	Initial release
27-Jul-2015	2	Updated Features , Table 2 , Table 7 , Figure 4 and torque value.

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